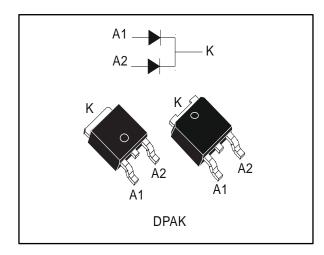
STPS640C



Power Schottky rectifier

Datasheet - production data



Features

- Very small conduction losses
- Extremely fast switching
- Low thermal resistance
- Negligible switching losses
- Low forward voltage drop
- Low capacitance
- Avalanche specification
- ECOPACK®2 compliant component for DPAK on demand

Description

This dual Schottky rectifier is designed for switch mode power supplies and other power converters.

This device is intended for use in low and medium voltage operation, and in particular high frequency circuits where low switching losses are required (free wheeling and polarity protection).

Table 1: Device summary

Symbol	Value
I _{F(AV)}	2 x 3 A
V_{RRM}	40 V
T _j (max)	150 °C
V _F (typ)	0.50 V

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1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, per diode, unless otherwise specified)

Symbol	Parameter	Value	Uni t	
V _{RRM}	Repetitive peak reverse voltage	40	V	
I _{F(RMS)}	Forward rms current	6	Α	
I _{F(AV)}	Average forward current δ = 0.5, square wave	3	Α	
I _{FSM}	Surge non repetitive forward current	75	Α	
P _{ARM}	Repetitive peak avalanche power $ \begin{array}{c} tp = 10 \; \mu s \\ T_j = 125 \; ^{\circ}C \end{array} $		90	W
T _{stg}	Storage temperature range	-65 to +150	°C	
Tj	Maximum operating junction temperature (1)	150	°C	

Notes:

Table 3: Thermal parameters

Symbol	Parameter	Max. value	Unit	
В	Junction to case	Per diode	5.5	
R _{th(j-c)} Junction to case	Junction to case	Per device	3	°C/W
R _{th(c)}	Coupling		0.5	

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_{j \text{ (diode1)}} = P_{\text{(diode1)}} x R_{\text{th(j-c)}} \text{ (per diode)} + P_{\text{(diode2)}} x R_{\text{th(c)}}$

Table 4: Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Devene legicone aumont	T _j = 25 °C	M M	-		100	μΑ
IR ^(*)	Reverse leakage current	T _j = 125 °C	$V_R = V_{RRM}$	-	2	10	mA
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	I _F = 3 A	-		0.63	V
		T _j = 125 °C		-	0.50	0.57	
		T _j = 25 °C	I _F = 6 A	-		0.84	V
		T _j = 125 °C		-	0.67	0.72	

Notes:

 $^{(1)}Pulse$ test: t_p = 5 ms, δ < 2%

 $^{(2)}$ Pulse test: t_p = 380 μ s, δ < 2%

To evaluate the conduction losses, use the following equation:

 $P = 0.42 \text{ x } I_{F(AV)} + 0.050 \text{ x } I_{F^2(RMS)}$

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 $^{^{(1)}(}dP_{tot}/dT_j) < (1/R_{th(j-a)}) \ condition \ to \ avoid \ thermal \ runaway \ for \ a \ diode \ on \ its \ own \ heatsink.$

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δ=tp/T

3.5

3.0

1.1 Characteristics (curves)

1.25 1.00

0.75

0.50 0.25

0.00

Figure 1: Average forward power dissipation versus average forward current(per diode) $P_{F(AV)}(W)$ 2.50 0.05

temperature (per diode, $\delta = 0.5$) $I_{\mathsf{F}(\mathsf{AV})}(\mathsf{A})$ 4.0 R_{th(j-a)} = R_{th(j-c)} 3.5 3.0 2.5 2.0 1.5 1.0 0.5 T_{amb}(°C) δ= tp/T 0.0 0 25 50 75 100 125 150

Figure 2: Average forward current versus ambient

Figure 3: Normalized avalanche power derating versus pulse duration (T_j = 125 °C)

2.0

2.5

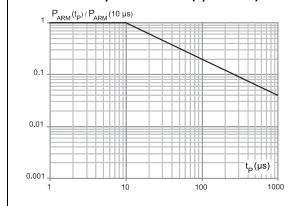


Figure 4: Relative variation of thermal impedance junction to case versus pulse duration

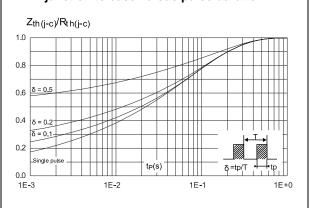


Figure 5: Reverse leakage current versus reverse voltage applied (typical values, per diode)

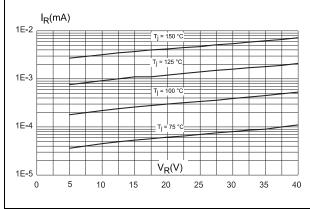
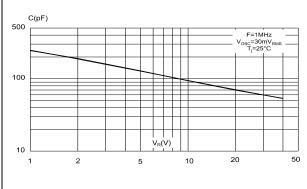


Figure 6: Junction capacitance versus reverse voltage applied (typical values, per diode)



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Figure 7: Forward voltage drop versus forward current (maximum values, per diode)

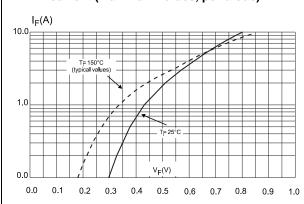
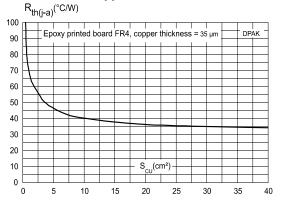


Figure 8: Thermal resistance junction to ambient versus copper surface under tab



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STPS640C Package information

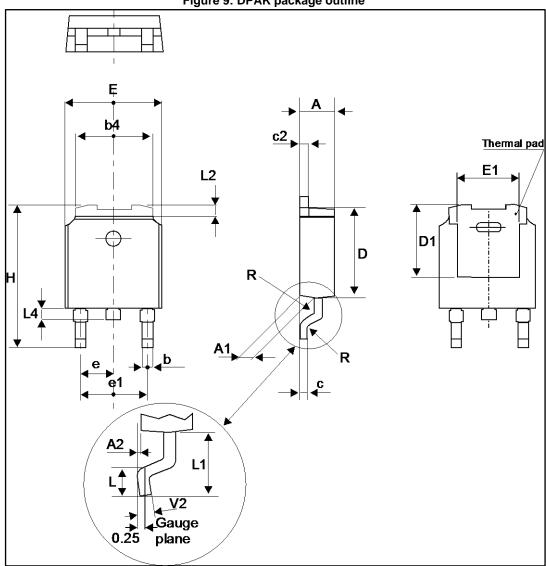
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Cooling method: by conduction (C)
- Epoxy meets UL 94,V0

2.1 DPAK package information

Figure 9: DPAK package outline





This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.



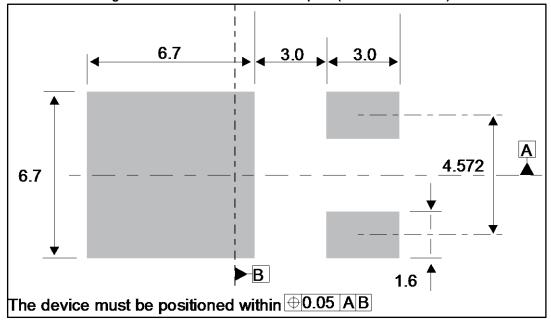
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Table 5: DPAK package mechanical data

	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	2.18	2.40	0.085	0.094	
A1	0.90	1.10	0.035	0.043	
A2	0.03	0.23	0.001	0.009	
b	0.64	0.90	0.025	0.035	
b4	4.95	5.46	0.194	0.215	
С	0.46	0.61	0.018	0.024	
c2	0.46	0.60	0.018	0.023	
D	5.97	6.22	0.235	0.244	
D1	4.95	5.60	0.194	0.220	
Е	6.35	6.73	0.250	0.265	
E1	4.32	5.50	0.170	0.216	
е	2.2	86 typ.	0.090	typ.	
e1	4.40	4.70	0.173	0.185	
Н	9.35	10.40	0.368	0.409	
L	1.0	1.78	0.039	0.070	
L2		1.27		0.050	
L4	0.60	1.02	0.023	0.040	
V2	-8°	+8°	-8°	+8°	

Figure 10: DPAK recommended footprint (dimensions in mm)



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STPS640C Ordering information

3 Ordering information

Table 6: Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS640CB	S6 40C	DDAK	0.22.4	75	Tube
STPS640CB-TR	S6 40C	DPAK	0.32 g	2500	Tape and reel

4 Revision history

Table 7: Document revision history

Date	Revision	Changes
Aug-2003	6B	Last issue
22-Mar-2007	7	Updated Figure 8 Updated ECOPACK statement.
20-Nov-2014	8	Figure 3. Removed PARM (Tj = 25 °C), TO-220AB and TO-220FPAB package information.
16-May-2017	9	Updated DPAK package information and reformatted to current standard.



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